

IR155DM16CCB SERIES

STANDARD RECOVERY DIODES

■ Junction Size: Square 155 mils

■ Wafer Size: 4"

■ V_{RRM} Class: 1600 V

■ Passivation Process: Glassivated MOAT

■ Reference IR Packaged Part: 15ETS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions	
V _{FM} Maximum Forward Voltage	1100 mV	$T_J = Amb., I_F = 15 A$	
V _{RRM} Reverse Breakdown Voltage Range	1600 V (*)	$T_J = Amb., I_{RRM} = 50 \mu A$	(**)

^(*) Wafer and die Probe test clamped at 1200V to limit arcing. 1600V BV testable only in encapsulated packages

Mechanical Characteristics

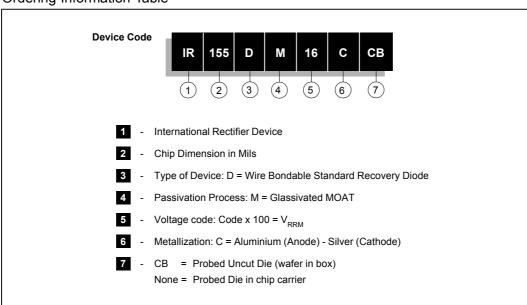
Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1 KA-4 KA-6 KA)	
Nominal Front Metal Composition, Thickness	100% AI, (20 μm)	
Chip Dimensions	155 x 155 mils (see drawing)	
Wafer Diameter	100 mm, with std. < 110 > flat	
Wafer Thickness	330 μm, ± 10 μm	
Maximum Width of Sawing Line	110 µm	
Reject Ink Dot Size	0.25 mm diameter minimum	
Ink Dot Location	Seedrawing	
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination	

^(**) Nitrogen flow on die edge.

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Preliminary Data Sheet I0146J 02/02

Ordering Information Table



Outline Table

